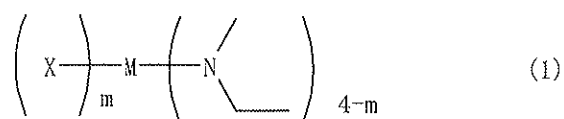


ABSTRACT

A novel metal compound of general formula (1), a material for chemical vapor phase growth containing the compound, and a process for forming a metal-containing thin film by chemical vapor phase growth using the material. Among the compounds of formula (1), those wherein X is a chlorine atom are preferred because of inexpensiveness and high volatility. When M is titanium, those wherein m is 1 are preferred as having a greater difference between a volatilization temperature (vapor temperature) and a deposition temperature (reaction temperature), which provides a broader process margin.



In formula (1), M is titanium, zirconium, or hafnium; X is a halogen atom; and m is 1 or 2.